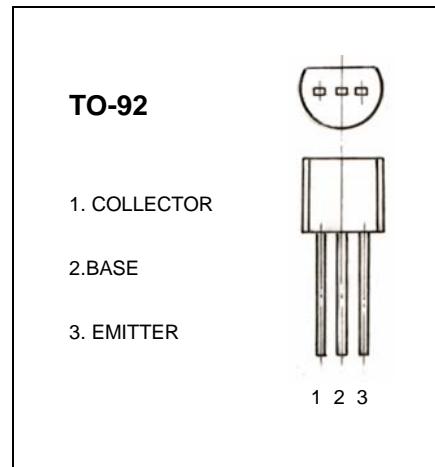


**BC337/BC338 TRANSISTOR (NPN)****FEATURES**

Power dissipation

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage BC337	50	V
	BC338	30	
V_{CEO}	Collector-Emitter Voltage BC337	45	V
	BC338	25	
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	800	mA
P_D	Total Device Dissipation	625	mW
T_j	Junction Temperature	150	°C
T_{stg}	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage BC337 BC338	V_{CBO}	$I_C= 100\mu\text{A}, I_E=0$	50 30			V
Collector-emitter breakdown voltage BC337 BC338	V_{CEO}	$I_C= 10\text{mA}, I_B=0$	45 25			V
Emitter-base breakdown voltage	V_{EBO}	$I_E= 10\mu\text{A}, I_C=0$	5			V
Collector cut-off current BC337 BC338	I_{CBO}	$V_{CB}= 45\text{V}, I_E=0$ $V_{CB}= 25\text{V}, I_E=0$			0.1 0.1	uA
Collector cut-off current BC337 BC338	I_{CEO}	$V_{CE}= 40\text{V}, I_B=0$ $V_{CE}= 20\text{V}, I_B=0$			0.2 0.2	uA
Emitter cut-off current	I_{EBO}	$V_{EB}= 4 \text{ V}, I_C=0$			0.1	uA
BC337/BC338 BC337-16/BC338-16 BC337-25/BC338-25 BC337-40/BC338-40	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C= 100\text{mA}$	100 100 160 250		630 250 400 630	
DC current gain	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C= 300\text{mA}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B= 50\text{mA}$			0.7	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C= 500\text{mA}, I_B=50\text{mA}$			1.2	V
Base-emitter voltage	V_{BE}	$V_{CE}=1\text{V}, I_C= 300\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}= 5\text{V}, I_C= 10\text{mA}$ $f = 100\text{MHz}$	210			MHz
Collector Output Capacitance	Cob	$V_{CB}=10\text{V}, I_E=0$ $f=1\text{MHz}$		15		pF